

www.vishay.com

Vishay Siliconix

P-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SU	JMMARY	
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^d
-40	$0.0042 \text{ at V}_{GS} = -10 \text{ V}$	-110
-40	0.0062 at V _{GS} = -4.5 V	-110

FEATURES

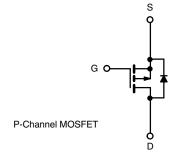
- TrenchFET® Power MOSFET
- Low thermal resistance











Ordering Information:

SUM110P04-04L-E3 (Lead (Pb)-free)

ABSOLUTE MAXIMUM RATINGS (T _C =	= 25 °C, unless otherw	rise noted)		
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	-40	V
Gate-Source Voltage		V _{GS}	± 20	v
Continuous Drain Current (T,I = 175 °C) d	T _C = 25 °C		-110	
Continuous Drain Current (1) = 175 C) °	T _C = 125 °C	l l ^D	-110	A
Pulsed Drain Current		I _{DM}	-240	_ A
Avalanche Current	L = 0.1 mH	I _{AS}	-75	
Single Pulse Avalanche Energy ^a	L = 0.1 IIII	E _{AS}	281	mJ
Dower Discinstion	T _C = 25 °C	PD	375 ^c	w
Power Dissipation	T _A = 25 °C b		3.75	vv
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction-to-Ambient PCB Mount ^b	R _{thJA}	40	°C/W	
Junction-to-Case	R_{thJC}	0.4	C/VV	

Notes

- a. Duty cycle ≤ 1 %.
- b. When mounted on 1" square PCB (FR-4 material).
- c. See SOA curve for voltage derating.
- d. Limited by package.



Vishay Siliconix

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static	•						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-40			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	-1		-3	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V _{DS} = -40 V, V _{GS} = 0 V			-1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -40 V, V _{GS} = 0 V, T _J = 125 °C			-50	μΑ	
		V _{DS} = -40 V, V _{GS} = 0 V, T _J = 175 °C			-250		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	-120			Α	
		V _{GS} = -10 V, I _D = -30 A		0.0034	0.0042		
Drain-Source On-State Resistance a		V _{GS} = -10 V, I _D = -30 A, T _J = 125 °C			0.0063	Ω	
Drain-Source On-State Resistance 4	R _{DS(on)}	V _{GS} = -10 V, I _D = -30 A, T _J = 175 °C			0.0076		
		$V_{GS} = -4.5 \text{ V}, I_D = -20 \text{ A}$		0.005	0.0062		
Forward Transconductance ^a	9fs	V _{DS} = -15 V, I _D = -30 A	20			S	
Dynamic ^b							
Input Capacitance	C _{iss}			11 200			
Output Capacitance	Coss	$V_{GS} = 0 \text{ V}, V_{DS} = -25 \text{ V}, f = 1 \text{ MHz}$		1650		pF	
Reverse Transfer Capacitance	C _{rss}			1200			
Total Gate Charge ^c	Qg			235	350		
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = -20 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -110 \text{ A}$		45		nC	
Gate-Drain Charge ^c	Q_{gd}			65			
Gate Resistance	R_g			3		Ω	
Turn-On Delay Time ^c	t _{d(on)}			25	40		
Rise Time ^c	t _r	$V_{DD} = -20 \text{ V}, R_1 = 0.18 \Omega$		30	45		
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong -110 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 2.5 \Omega$		190	300	ns	
Fall Time ^c	t _f			110	165		
Source-Drain Diode Ratings and Cha	racteristics	(T _C = 25 °C) ^b					
Continuous Current	I _S				-110	^	
Pulsed Current	I _{SM}				-240	Α	
Forward Voltage ^a	V_{SD}	$I_F = -85 \text{ A}, V_{GS} = 0 \text{ V}$		-1	-1.5	V	
Reverse Recovery Time	t _{rr}			65	100	ns	
Peak Reverse Recovery Current	I _{RM(REC)}	I _F = -85 A, dl/dt = 100 A/μs		-3.7	-5.6	Α	
Reverse Recovery Charge	Q _{rr}			0.12	0.28	μC	

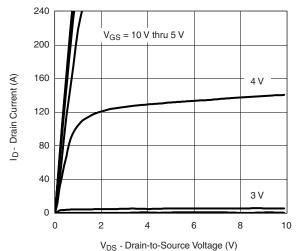
Notes

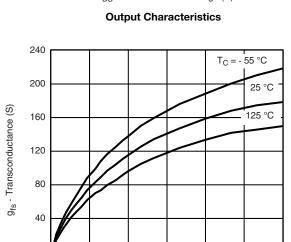
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





Transconductance

45

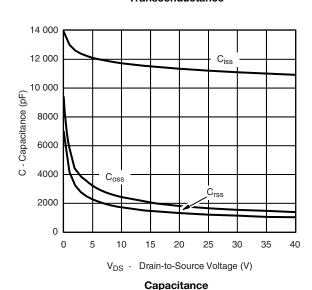
Drain Current (A)

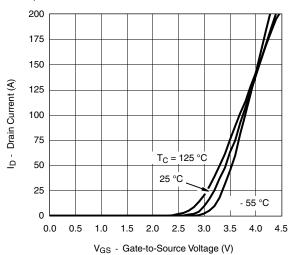
75

90

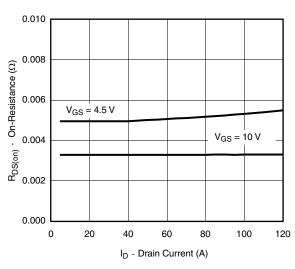
0

15

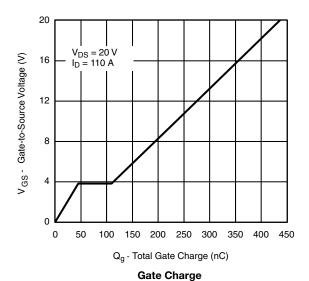




Transfer Characteristics

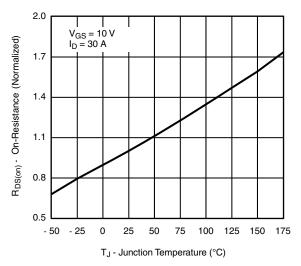


On-Resistance vs. Drain Current

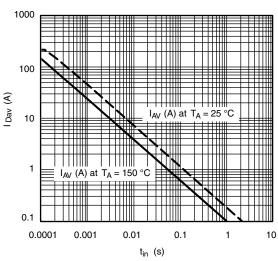




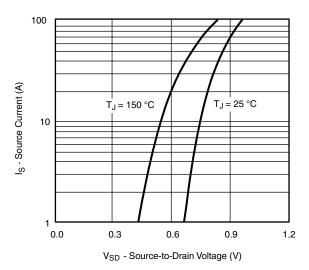
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



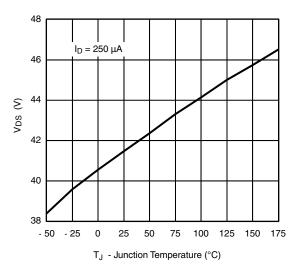
On-Resistance vs. Junction Temperature



Avalanche Current vs. Time



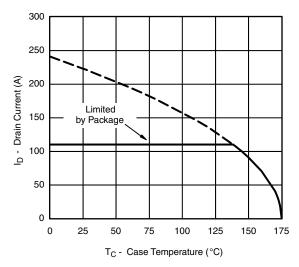
Source-Drain Diode Forward Voltage



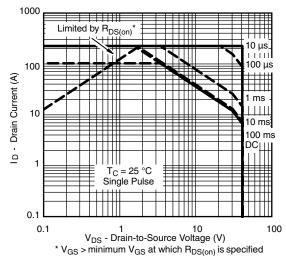
Drain Source Breakdown vs. Junction Temperature



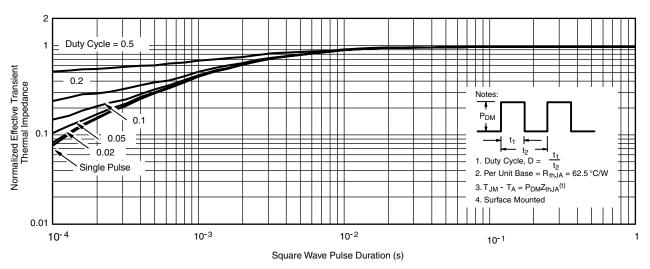
THERMAL RATINGS



Maximum Avalanche and Drain Current vs. Case Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

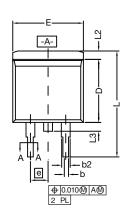
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?72437.

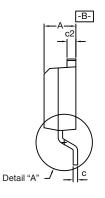
Vishay Siliconix

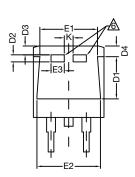


TO-263 (D²PAK): 3-LEAD

VERSION 1: FACILITY CODE = T

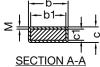








DETAIL A (ROTATED 90°)



≥ <u>↓</u>			ţ
< T		10	ပ
SF	CTION	1	1

Notes

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6. This feature is for thick lead.

		INC	HES	MILLIN	METERS	
	DIM.	MIN.	MAX.	MIN.	MAX.	
	Α	0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457	
١	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
Ü	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
	D2	0.038	0.042	0.965	1.067	
	D3	0.045	0.055	1.143	1.397	
	D4	0.044	0.052	1.118	1.321	
	E	0.380	0.410	9.652	10.414	
	E1	0.245	-	6.223	-	
	E2	0.355	0.375	9.017	9.525	
	E3	0.072	0.078	1.829	1.981	
	е	0.100	BSC	2.54	BSC	
	K	0.045	0.055	1.143	1.397	
	L	0.575	0.625	14.605	15.875	
	L1	0.090	0.110	2.286	2.794	
	L2	0.040	0.055	1.016	1.397	
	L3	0.050	0.070	1.270	1.778	
	L4	0.010	BSC	0.254	BSC	
	М	-	0.002	-	0.050	

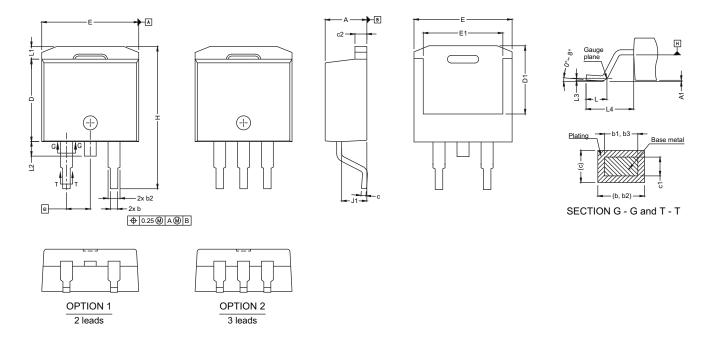
Revison: 28-Oct-2024 Document Number: 71198



www.vishay.com

Vishay Siliconix

VERSION 2: FACILITY CODE = N



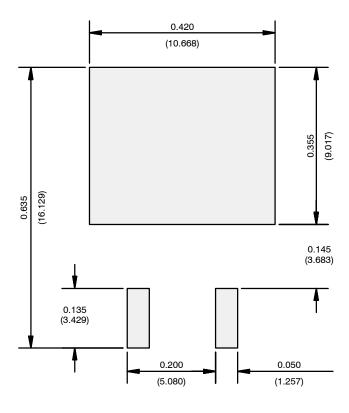
DIM.	MIN.	MAX.
A	4.36	4.56
A1	0	0.25
b	0.70	0.90
b1	0.51	0.89
b2	1.20	1.46
b3	1.17	1.37
С	0.38	0.694
c1	0.38	0.534
c2	1.19	1.34
D	8.60	9.00
D1	6.9	7.5
E	10.15	10.55
E1	8.1	8.7
е	2.54	BSC
Н	15.0	15.6
L	1.9	2.5
L1	-	1.65
L2	-	1.78
L3	0.25	5 typ.
L4	4.78	5.28
J1	2.56	2.96

DWG: 5843





RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index



Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Vishay products are not designed for use in life-saving or life-sustaining applications or any application in which the failure of the Vishay product could result in personal injury or death unless specifically qualified in writing by Vishay. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.